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Properties of AlN_x thin films prepared by DC reactive magnetron sputtering

Andrzej Stafiniak, Donata Muszynska, Adam Szyszka, Bogdan Paszkiewicz, Konrad Ptasinski, Sergiusz Patela, Regina Paszkiewicz, Marek Tlaczala

Keywords

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Abstract

In this paper, the results of investigation of the influence of cathode current on optical and dielectric AlN_x thin-film properties are presented. AlN_x films were prepared by pulsed DC reactive magnetron sputtering of Al target on substrates at room temperature. For characterization of fabricated test structures *C-V* spectroscopy, ellipsometry measurement and atomic force microscopy (AFM) were used.